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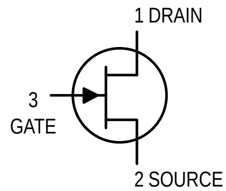
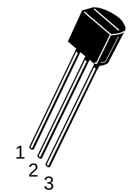
JFETs Switching
N–Channel — Depletion

2N5640





CASE 29–04, STYLE 5
TO–92 (TO–226AA)

Rating	Symbol	Value	Unit
Drain–Source Voltage	V_{DS}	30	Vdc
Drain–Gate Voltage	V_{DG}	30	Vdc
Reverse Gate–Source Voltage	V_{GSR}	30	Vdc
Forward Gate Current	I_{GF}	10	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	350 2.8	mW mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	357	°C/W
Junction Temperature Range	T_J	–65 to +150	°C
Storage Temperature Range	T_{stg}	–65 to +150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Gate–Source Breakdown Voltage (I_G = 10 μAdc, V_{DS} = 0)	$V_{(BR)GSS}$	30	—	Vdc
Gate Reverse Current (V_{GS} = –15 Vdc, V_{DS} = 0) (V_{GS} = –15 Vdc, V_{DS} = 0, T_A = 100°C)	I_{GSS}	 — —	 1.0 1.0	 nAdc μAdc
Drain Cutoff Current (V_{DS} = 15 Vdc, V_{GS} = –6.0 Vdc) (V_{DS} = 15 Vdc, V_{GS} = –6.0 Vdc, T_A = 100°C)	$I_{D(off)}$	 — —	 1.0 1.0	 nAdc μAdc
ON CHARACTERISTICS				
Zero–Gate–Voltage Drain Current(1) (V_{DS} = 20 Vdc, V_{GS} = 0)	I_{DSS}	5.0	—	mAdc
Drain–Source On–Voltage (I_D = 3.0 mAdc, V_{GS} = 0)	$V_{DS(on)}$	—	0.5	Vdc
Static Drain–Source On Resistance (I_D = 1.0 mAdc, V_{GS} = 0)	$r_{DS(on)}$	—	100	Ohms

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 3.0%.

REV 1

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Continued)

Characteristic			Symbol	Min	Max	Unit
SMALL–SIGNAL CHARACTERISTICS						
Static Drain–Source “ON” Resistance (V_{GS} = 0, I_D = 0, f = 1.0 kHz)			$r_{ds(on)}$	—	100	Ohms
Input Capacitance (V_{DS} = 0, V_{GS} = –12 Vdc, f = 1.0 MHz)			C_{iss}	—	10	pF
Reverse Transfer Capacitance (V_{DS} = 0, V_{GS} = –12 Vdc, f = 1.0 MHz)			C_{rss}	—	4.0	pF
SWITCHING CHARACTERISTICS						
Turn–On Delay Time	V_{DD} = 10 Vdc, $V_{GS(on)}$ = 0, $V_{GS(off)}$ = –10 Vdc, R_G' = 50 Ω	$I_{D(on)}$ = 3.0 mAdc	$t_{d(on)}$	—	8.0	ns
Rise Time		$I_{D(on)}$ = 3.0 mAdc	t_r	—	10	ns
Turn–Off Delay Time		$I_{D(on)}$ = 3.0 mAdc	$t_{d(off)}$	—	15	ns
Fall Time		$I_{D(on)}$ = 3.0 mAdc	t_f	—	30	ns

TYPICAL SWITCHING CHARACTERISTICS

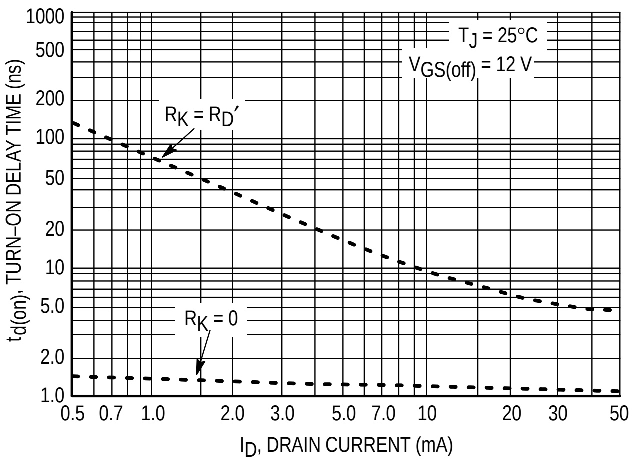


Figure 1. Turn–On Delay Time

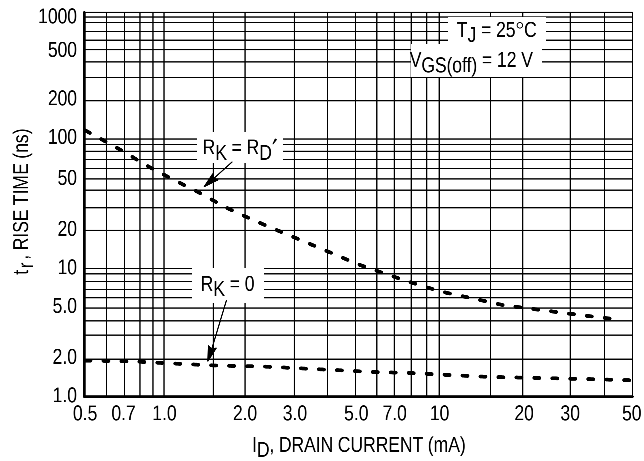


Figure 2. Rise Time

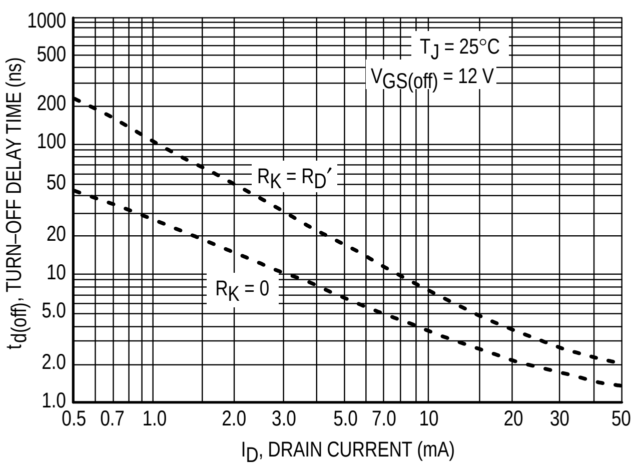


Figure 3. Turn–Off Delay Time

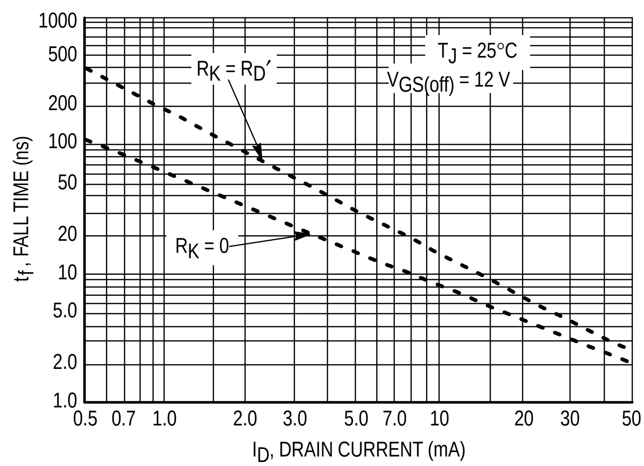


Figure 4. Fall Time

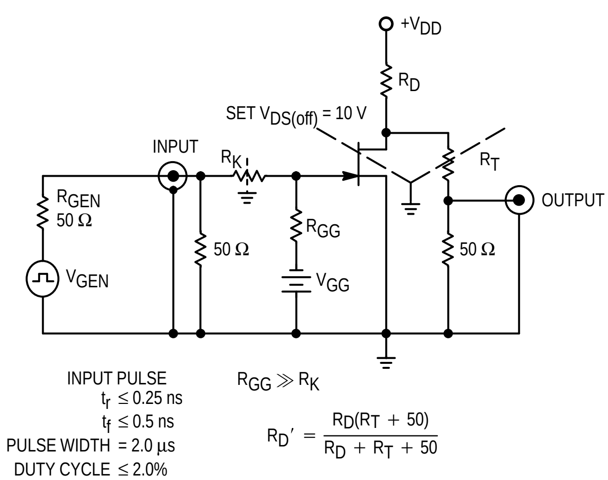


Figure 5. Switching Time Test Circuit

NOTE 1

The switching characteristics shown above were measured using a test circuit similar to Figure 5. At the beginning of the switching interval, the gate voltage is at Gate Supply Voltage ($-V_{GG}$). The Drain–Source Voltage (V_{DS}) is slightly lower than Drain Supply Voltage (V_{DD}) due to the voltage divider. Thus Reverse Transfer Capacitance (C_{rss}) or Gate–Drain Capacitance (C_{gd}) is charged to $V_{GG} + V_{DS}$.

During the turn–on interval, Gate–Source Capacitance (C_{gs}) discharges through the series combination of R_{Gen} and R_K. C_{gd} must discharge to $V_{DS(on)}$ through R_G and R_K in series with the parallel combination of effective load impedance (R'_D) and Drain–Source Resistance (r_{ds}). During the turn–off, this charge flow is reversed.

Predicting turn–on time is somewhat difficult as the channel resistance r_{ds} is a function of the gate–source voltage. While C_{gs} discharges, V_{GS} approaches zero and r_{ds} decreases. Since C_{gd} discharges through r_{ds}, turn–on time is non–linear. During turn–off, the situation is reversed with r_{ds} increasing as C_{gd} charges.

The above switching curves show two impedance conditions; 1) R_K is equal to R_D, which simulates the switching behavior of cascaded stages where the driving source impedance is normally the load impedance of the previous stage, and 2) R_K = 0 (low impedance) the driving source impedance is that of the generator.

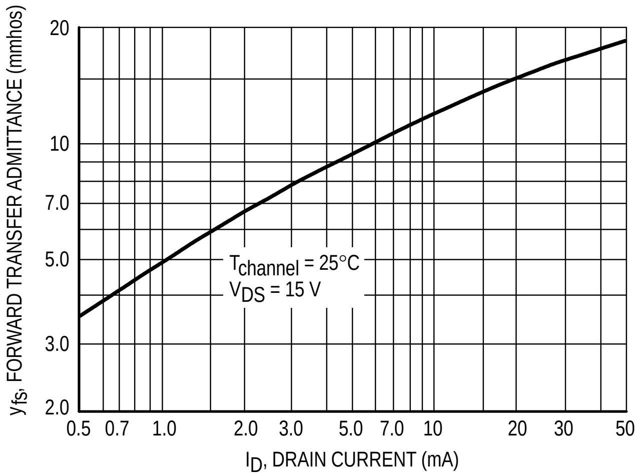


Figure 6. Typical Forward Transfer Admittance

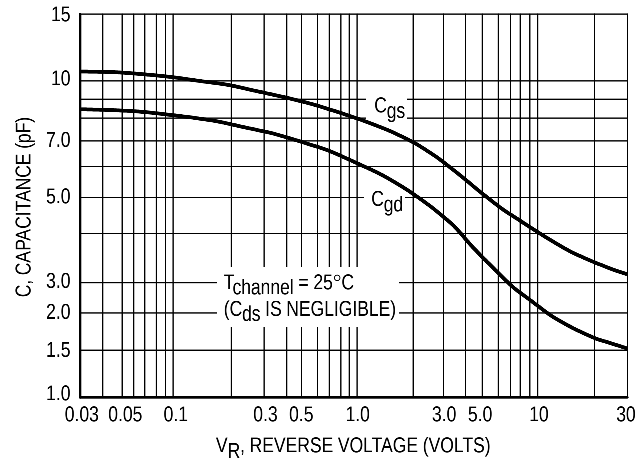


Figure 7. Typical Capacitance

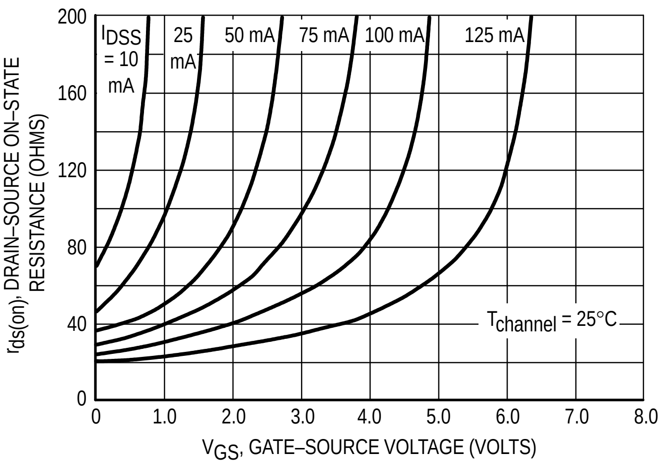


Figure 8. Effect of Gate–Source Voltage On Drain–Source Resistance

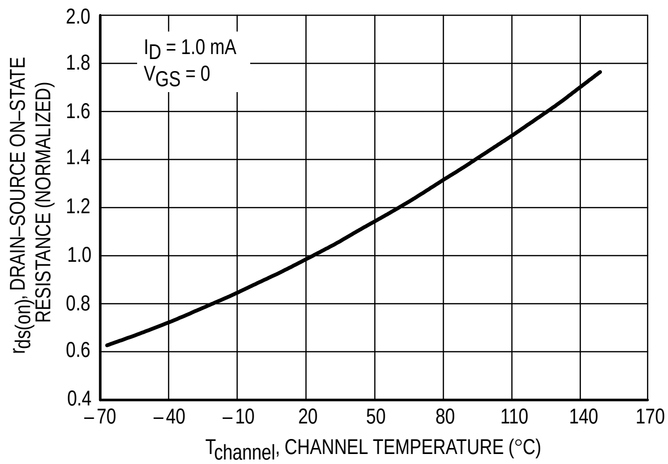


Figure 9. Effect of Temperature On Drain–Source On–State Resistance

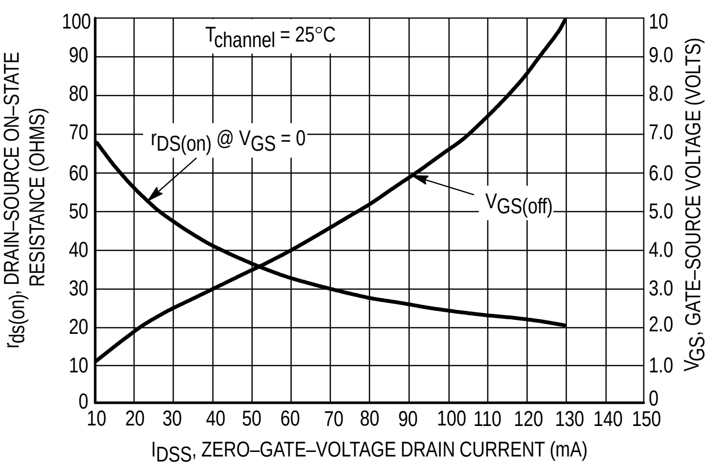
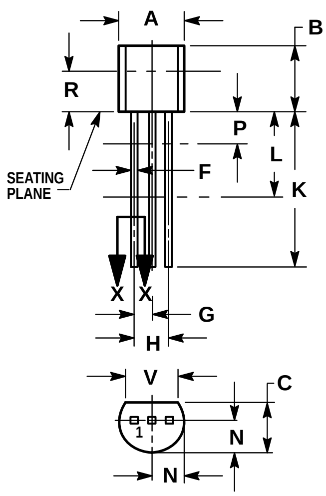


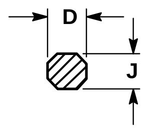
Figure 10. Effect of I_{DSS} On Drain–Source Resistance and Gate–Source Voltage

NOTE 2

The Zero–Gate–Voltage Drain Current (I_{DSS}), is the principle determinant of other J-FET characteristics. Figure 10 shows the relationship of Gate–Source Off Voltage ($V_{GS(off)}$ and Drain–Source On Resistance ($r_{ds(on)}$) to I_{DSS}. Most of the devices will be within ±10% of the values shown in Figure 10. This data will be useful in predicting the characteristic variations for a given part number.

PACKAGE DIMENSIONS





SECTION X–X

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSION D AND J APPLY BETWEEN L AND K MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.022	0.41	0.55
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	—	12.70	—
L	0.250	—	6.35	—
N	0.080	0.105	2.04	2.66
P	—	0.100	—	2.54
R	0.115	—	2.93	—
V	0.135	—	3.43	—

STYLE 5:
PIN 1. DRAIN
2. SOURCE
3. GATE

CASE 029–04
(TO–226AA)
ISSUE AD

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